IN THE CLAIMS

1. (Currently amended) A semiconductor device having a pad region and a circuit region, comprising:

a low-k dielectric film on [a] the pad region and [a] the circuit region a substrate, the low-k dielectric film having a dielectric constant of no more than 3;

an insulating film on the low-k dielectric film of the pad region, the insulating film having higher strength than the low-k dielectric film;

multi-layer wirings on the insulating film of the pad region and on the low-k dielectric film of the circuit region; and

a bonding pad on an outermost wiring of the multi-layer wirings of the pad region.

2. (Currently amended) The semiconductor device according to claim 1, wherein sidewalls of the wirings in the pad region are surrounded by the insulating film.

3. (Previously presented) The semiconductor device according to claim 1, wherein the low-k dielectric film is an insulating film containing silicon, carbon, oxygen, and hydrogen.

4. (Currently amended) A semiconductor device having a pad region and a circuit region, comprising:

multi-layer low-k dielectric films on [a]the pad region and [a]the circuit region of a substrate, each of the multi-layer low-k dielectric films having a dielectric constant of no more than 3;

insulating films on each of the multi-layer low-k dielectric films of the pad region, each of the insulating films having higher strength than each of the multi-layer low-k dielectric films;

wirings on each of the insulating films of the pad region and on each of the low-k dielectric films of the circuit region; and

a bonding pad on an outermost wiring of the wirings of the pad region.

5. (Previously presented) The semiconductor device according to claim 4, wherein sidewalls of the wirings in the pad region are surrounded by the insulating films.

PAGE 3/5 * RCVD AT 4/25/2005 7:09:25 PM [Eastern Daylight Time] * SVR:USPTO-EFXRF-1/5 * DNIS:8729306 * CSID:5032744622 * DURATION (mm-ss):01-58

Claims 6-9 (cancelled)

10. (Previously presented) The semiconductor device according to claim 1, wherein the low-k dielectric film is a polymer film containing hydrogen and carbon.

PAGE 4/5 * RCVD AT 4/25/2005 7:09:25 PM [Eastern Daylight Time] * SVR:USPTO-EFXRF-1/5 * DNIS:8729306 * CSID:5032744622 * DURATION (mm-ss):01-58